

## **isc Silicon NPN Darlington Power Transistor**

**BD897** 

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min)
- · High DC Current Gain
  - : h<sub>FE</sub>= 750(Min) @I<sub>C</sub>= 3A
- · Collector Power Dissipation-
- : P<sub>C</sub>= 70W@ T<sub>C</sub>= 25℃
- 8 A Continuous Collector Current
- Complement to Type BD898
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



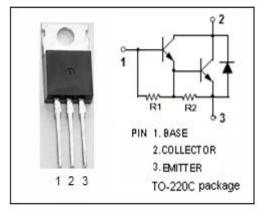
 Designed for use as complementary AF push-pull output stage applications

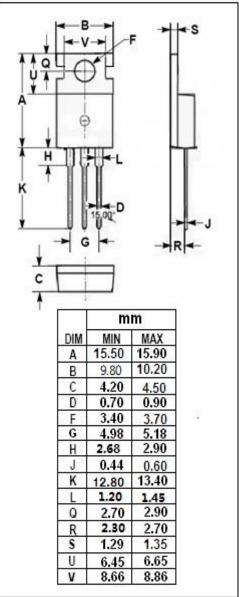
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	5 V	
Ic	Collector Current-Continuous	8	Α	
I <sub>B</sub>	Base Current-Continuous	0.3	Α	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	10/	
	Collector Power Dissipation @ T <sub>C</sub> =25℃	70	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.79	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient		°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 12mA			2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= 3A; Vc= 3V			2.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0		2.0		
		V <sub>CB</sub> = 60V; I <sub>E</sub> = 0; T <sub>C</sub> = 100 °C			2.0	- mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0			0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			2	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 3V	750			

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